

SPTECH Silicon PNP Power Transistor**2SA1080****DESCRIPTION**

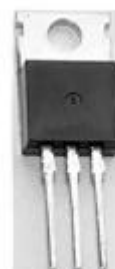
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -40V(\text{Min.})$
- Good Linearity of h_{FE}
- Complement to Type 2SC2530

APPLICATIONS

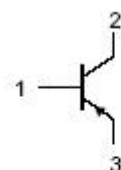
- Designed for medium power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

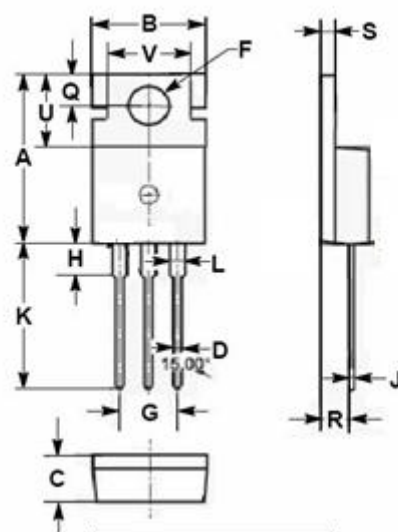
SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-0.5	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$



1 2 3



PIN 1. BASE
2. COLLECTOR
3. EMITTER
TO-220C package



DIM	mm	
	MIN	MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

SPTECH Silicon PNP Power Transistor**2SA1080****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA; R _{BE} = ∞	-40			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -0.1 μ A; I _E = 0	-40			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -0.1 μ A; I _C = 0	-7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -10mA; I _B = -1mA			-0.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -10mA; I _B = -1mA			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -40V; I _E = 0			-100	nA
I _{CEO}	Collector Cutoff Current	V _{CE} = -40V; I _B = 0			-500	nA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -7V; I _C = 0			-100	nA
h _{FE}	DC Current Gain	I _C = -10mA; V _{CE} = -5V	100		350	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -20V; f= 1.0MHz		65		pF
f _T	Current-Gain—Bandwidth Product	I _C = -10mA; V _{CE} = -10V; f=10MHz		30		MHz